

SGP23N60UF

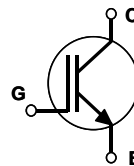
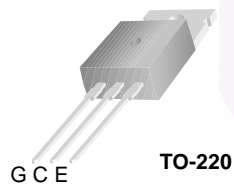
600V PT IGBT

General Description

Fairchild's UF series IGBTs provide low conduction and switching losses. UF series is designed for the applications such as general inverters and PFC where High Speed Switching is required feature.

Features

- 12 A, 600 V, $T_C = 100^\circ\text{C}$
- Low Saturation Voltage: $V_{CE(sat)} = 2.1\text{ V @ } I_C = 12\text{ A}$
- Typical Fall Time.220ns at $T_J = 125^\circ\text{C}$
- High Input Impedance



Applications

General Inverter, PFC

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	23	A
	Collector Current @ $T_C = 100^\circ\text{C}$	12	A
$I_{CM(1)}$	Pulsed Collector Current	92	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	100	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	40	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.2	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics of the IGBT $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

Off Characteristics

BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	600	--	--	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	--	0.6	--	$\text{V}/^\circ\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	--	--	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	--	--	± 100	nA

On Characteristics

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 12\text{ mA}, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 12\text{ A}, V_{GE} = 15\text{ V}$	--	2.1	2.6	V
		$I_C = 23\text{ A}, V_{GE} = 15\text{ V}$	--	2.6	--	V

Dynamic Characteristics

C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$	--	720	--	pF
C_{oes}	Output Capacitance		--	100	--	pF
C_{res}	Reverse Transfer Capacitance		--	25	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300\text{ V}, I_C = 12\text{ A},$ $R_G = 23\text{ }\Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	--	17	--	ns
t_r	Rise Time		--	27	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	130	ns
t_f	Fall Time		--	70	150	ns
E_{on}	Turn-On Switching Loss		--	115	--	μJ
E_{off}	Turn-Off Switching Loss		--	135	--	μJ
E_{ts}	Total Switching Loss		--	250	400	μJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300\text{ V}, I_C = 12\text{ A},$ $R_G = 23\text{ }\Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 125^\circ\text{C}$	--	23	--	ns
t_r	Rise Time		--	32	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	100	200	ns
t_f	Fall Time		--	220	250	ns
E_{on}	Turn-On Switching Loss		--	205	--	μJ
E_{off}	Turn-Off Switching Loss		--	320	--	μJ
E_{ts}	Total Switching Loss		--	525	800	μJ

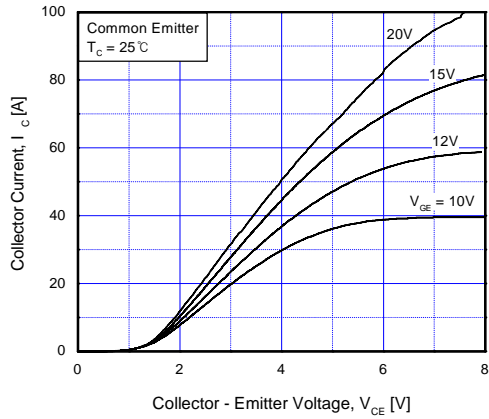


Fig 1. Typical Output Characteristics

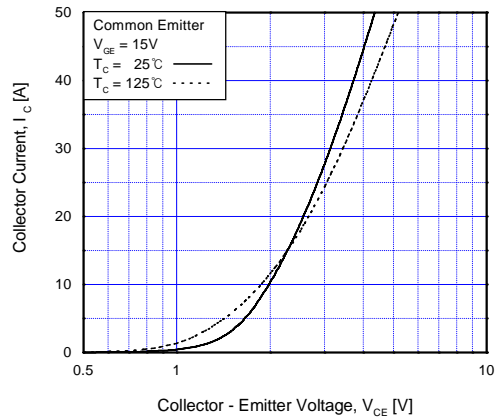


Fig 2. Typical Saturation Voltage Characteristics

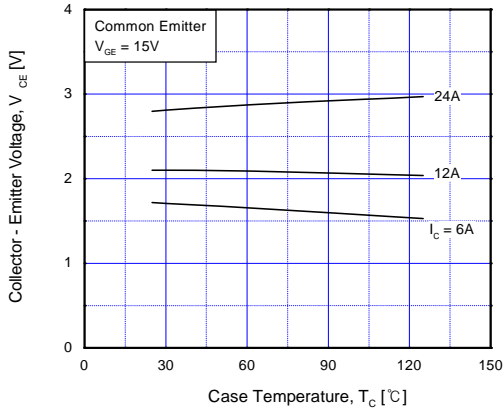


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

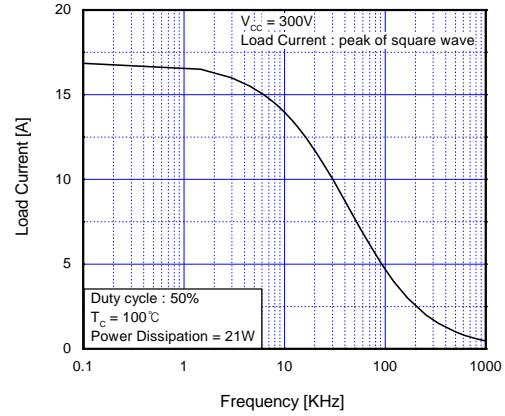


Fig 4. Load Current vs. Frequency

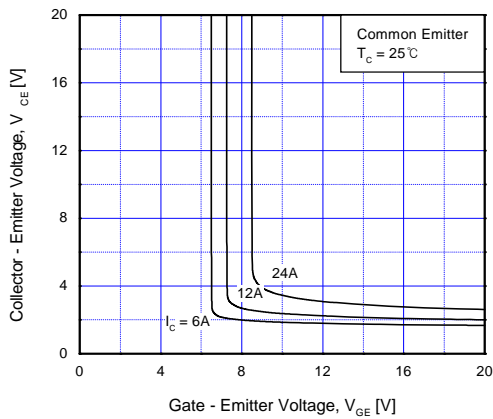


Fig 5. Saturation Voltage vs. V_{GE}

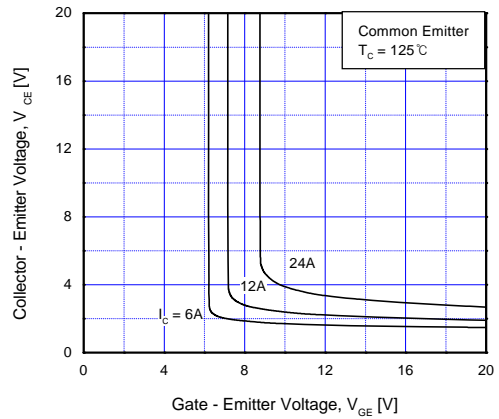


Fig 6. Saturation Voltage vs. V_{GE}

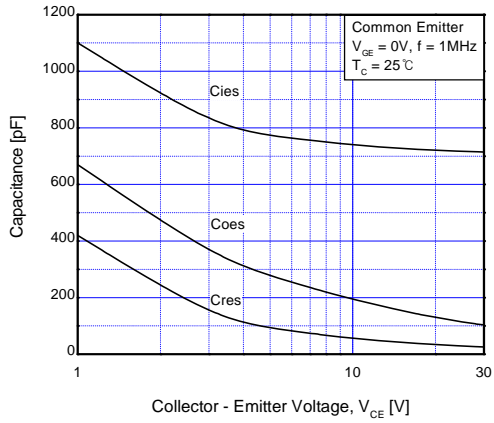


Fig 7. Capacitance Characteristics

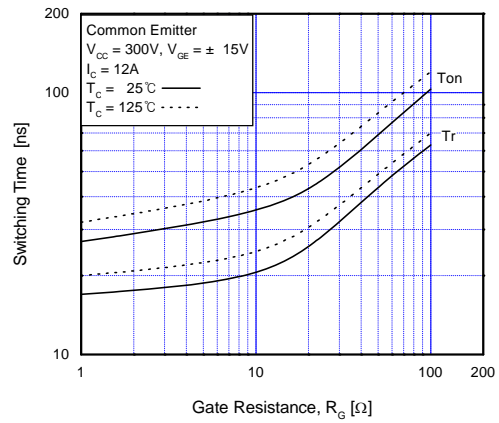


Fig 8. Turn-On Characteristics vs. Gate Resistance

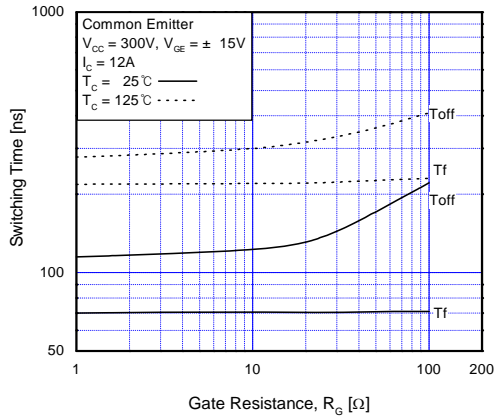


Fig 9. Turn-Off Characteristics vs. Gate Resistance

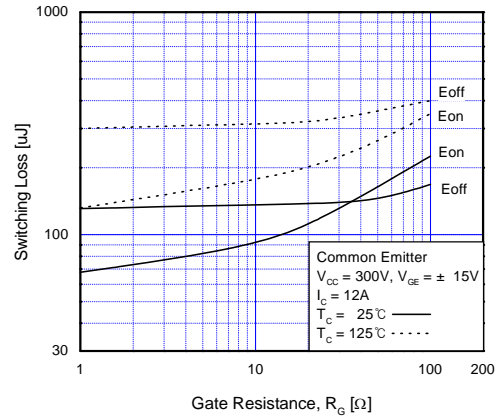


Fig 10. Switching Loss vs. Gate Resistance

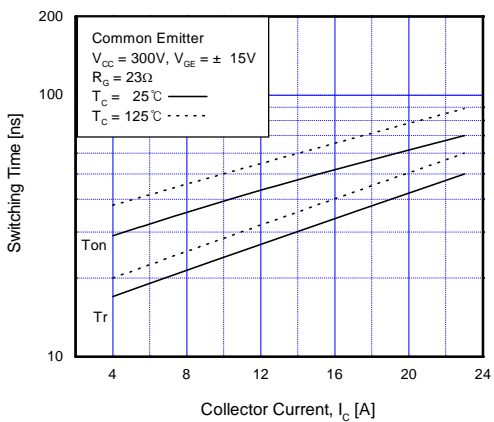


Fig 11. Turn-On Characteristics vs. Collector Current

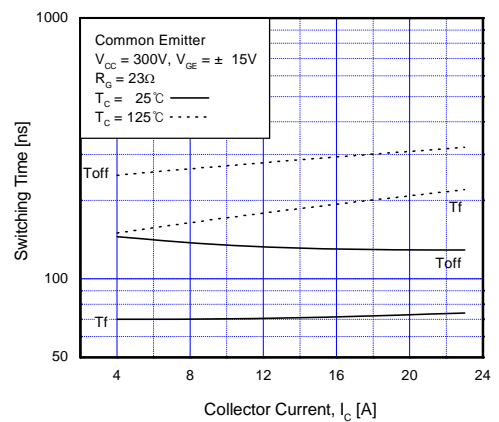


Fig 12. Turn-Off Characteristics vs. Collector Current

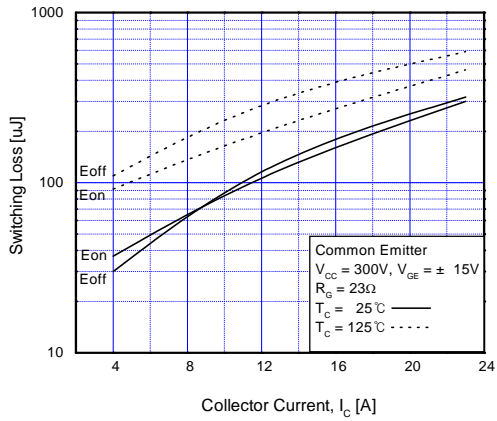


Fig 13. Switching Loss vs. Collector Current

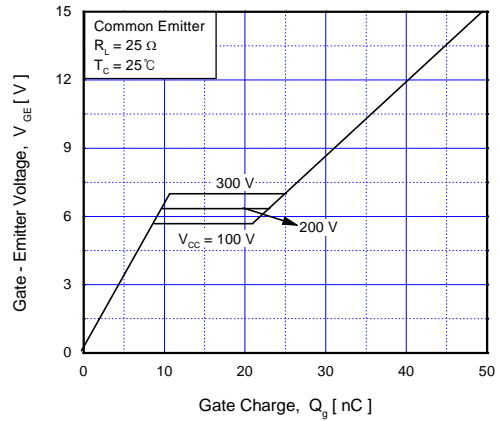


Fig 14. Gate Charge Characteristics

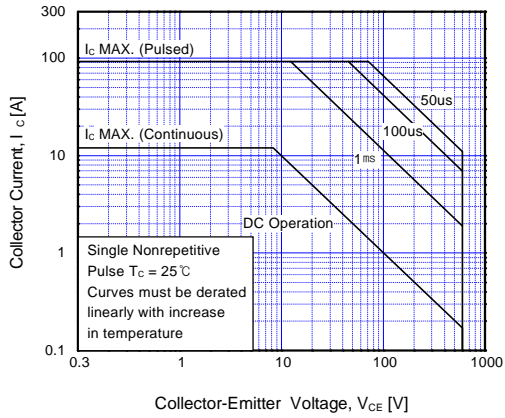


Fig 15. SOA Characteristics

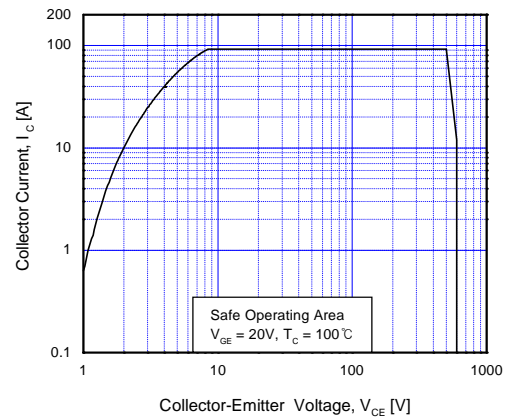


Fig 16. Turn-Off SOA Characteristics

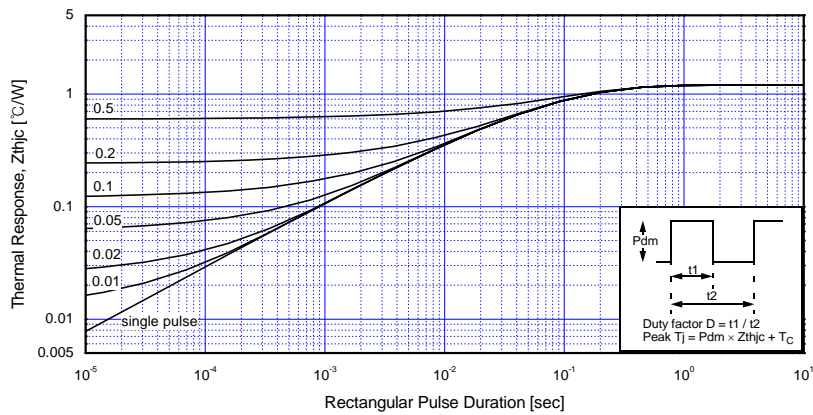


Fig 17. Transient Thermal Impedance of IGBT

Mechanical Dimensions

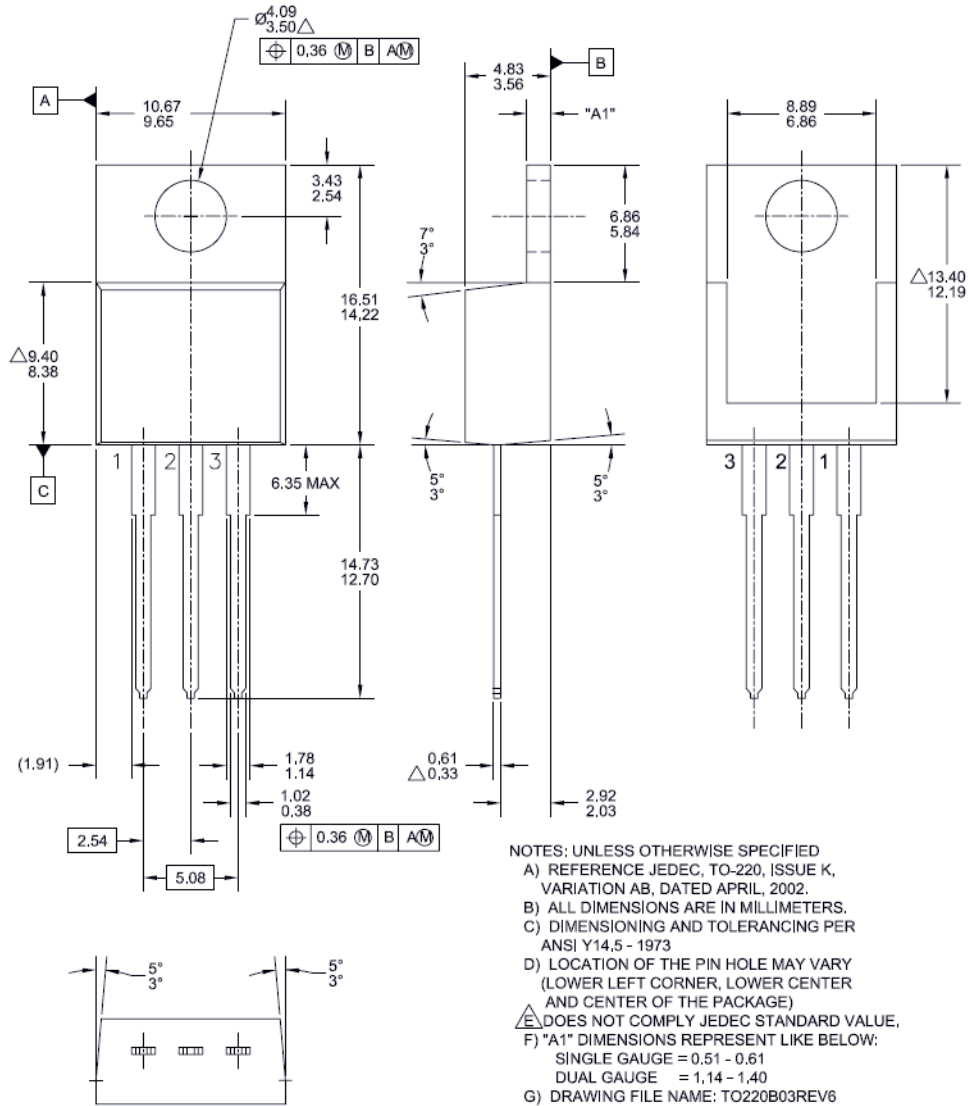


Figure 18. TO-220 3L - TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.





Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-003



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|--|---|---|--|
| AccuPower™ | F-PFST™ | PowerTrench® | Sync-Lock™ |
| AX-CAP®* | FRFET® | PowerXS™ |  SYSTEM®* |
| BitSiC™ | Global Power Resource SM | Programmable Active Droop™ | TinyBoost® |
| Build it Now™ | GreenBridge™ | QFET® | TinyBuck™ |
| CorePLUS™ | Green FPS™ | QS™ | TinyCalc™ |
| CorePOWER™ | Green FPS™ e-Series™ | Quiet Series™ | TinyLogic® |
| CROSSVOLT™ | Gmax™ | RapidConfigure™ | TINYOPTO™ |
| CTL™ | GTO™ | | TinyPower™ |
| Current Transfer Logic™ | IntelliMAX™ |  Saving our world, 1mW/W/kW at a time™ | TinyPWM™ |
| DEUXPEED® | ISOPLANAR™ | SignalWise™ | TranSiC™ |
| Dual Cool™ | Marking Small Speakers Sound Louder and Better™ | SmartMax™ | TriFault Detect™ |
| EcoSPARK® | MegaBuck™ | SMART START™ | TRUECURRENT®* |
| EfficientMax™ | MICROCOUPLER™ | Solutions for Your Success™ | µSerDes™ |
| ESBC™ | MicroFET™ | SPM® |  SerDes® |
|  Fairchild® | MicroPak™ | STEALTH™ | UHC® |
| Fairchild Semiconductor® | MicroPak2™ | SuperFET® | Ultra FRFET™ |
| FACT Quiet Series™ | MillerDrive™ | SuperSOT™-3 | UniFET™ |
| FACT® | MotionMax™ | SuperSOT™-6 | VCX™ |
| FAST® | mWSaver® | SuperSOT™-8 | VisualMax™ |
| FastvCore™ | OptoHit™ | SupreMOS® | VoltagePlus™ |
| FETBench™ | OPTOLOGIC® | SyncFET™ | XS™ |
| FPS™ | OPTOPLANAR® | | |

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support. Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I66